			<b>≥</b> √	
L	Hits	Search Text	DБ	Time stamp
Number				
1	520584	semiconductor or substrate	USPAT	2003/01/04
	1			13:47
2	177753	semiconductor adj substrate	USPAT;	2003/01/04
			US-PGPUB;	13:48
			EPO; JPO;	ļ
			DERWENT	
3	13869	(semiconductor adj substrate) and chamber	USPAT;	2003/01/04
•		,	US-PGPUB;	13:48
			EPO; JPO;	13.10
			DERWENT	
4	980	((semiconductor adj substrate) and	USPAT;	2003/01/04
		chamber) and (reservoir or tank)	US-PGPUB;	13:48
	i	(2002/022 02 04111)	EPO; JPO;	13.40
			DERWENT	
5	184	(((semiconductor adj substrate) and	USPAT;	2003/01/04
		chamber) and (reservoir or tank)) and	US-PGPUB;	14:04
	1	controller and valve	EPO; JPO;	14.04
		donorozior ana varvo	DERWENT	1
6	5390	(165/47,48.1,58,61,63,64,80.1,80.2,80.3,80		82003/01/04
Ü	0000	(103/4/,40.1,30,01,03,04,00.1,00.2,00.3,00	· d b B H 13) . CC1	14:05
7	5	((165/47,48.1,58,61,63,64,80.1,80.2,80.3,8	DIIODOM EV CC	
,	,	and substrate and chamber and (tank or	DOBPAU.5).CC	
		reservoir) and valve and controller		14:38
8	519			
0	319	Sublamanian.in.	USPAT	2003/01/04
9	1179			14:39
9	11/9	subramanian.in.	USPAT;	2003/01/04
			US-PGPUB;	14:43
			EPO; JPO;	
10	200	l , , , , , , , , , , , , , , , , , , ,	DERWENT	
10	307	subramanian.in. and (semiconductor or	USPAT;	2003/01/04
		resist)	US-PGPUB;	14:44
			EPO; JPO;	
			DERWENT	